REV LTR	DESCRIPTION	DATE	APPVD.
-	Orig. Release	01/15/06	JSN
А	Revised per ECN 2009-15	10/09/09	JSN
В	Revised per ECN 2010-7	6/21/10	JSN
С	Revised per ECN 2012-19	10/21/12	JSN
D	Revised per ECN 2013-17	11/01/13	JSN
E	Revised per ECN 2015-3	2/18/15	RTC
F	Revised per ECN 2018-16	11/15/18	RTC

# FTTC11 Series CMOS/LVDS/LVEPCL/CML Output TCXO/VCTCXO FOR SPACE APPLICATIONS 10MHz to 1500MHz

# (5 x 7 mm, SMD, 1.8V, 2.5 V, 3.3V)

(Refer to Page 5 for Models with Reduced Screening & QCI)

- SCOPE: FTTC11 series, CMOS/LVDS/CML/LVPECL output, high reliability hybrid microcircuit crystal oscillators aredesigned, produced and tested by Frequency Technology, Inc. as MIL-PRF-55310, Class "S" equivalentdevices for use in advanced military, avionics and space applications. These devices are of hybrid microcircuit technology conforming to MIL-PRF-55310, Type 1, Class 2 oscillators.
- 2. APPLICABLE DOCUMENTS:

MIL-PRF-55310EOscillator, Crystal Controlled, General Specifications forMIL-PRF-38534GHybrid Microcircuits, General Specifications forMIL-STD-883ETest Methods and Procedures for Microelectronics

- 3. REQUIREMENTS:
- 3.1 General: The individual item requirements shall be as specified herein.
- 3.2 Package: Ceramic, 90% Min.  $AL_2O_3$ . Thermal Resistance,  $\theta_{JC}$ : 50 °C / Watt.
- 3.2.1 Termination Finish: 1.3 μm minimum gold plate over 2.0 μm minimum nickel plate. Hot Solder tinning with Sn60/Pb40 solder per MIL-PRF-55310 is optional at an additional cost.
- 3.2.2 Weight: 0.60 Gms Max.
- 3.2.3 Reflow Soldering: Reflow soldering at 260 °C for 10 seconds shall not degrade the performance.
- 3.3 Hermeticity: Resistance welded, hermetically sealed, leak rate of  $1(10)^{-8}$  atm-cc/s Max.
- 3.4. Marking: As a minimum, the parts shall be marked with Fre-techP/N and date code
- 3.5 Absolute Maximum Ratings: Unless otherwise specified, absolute maximum ratings shall be as follows:

Supply Voltage	-0.5 to +4.0 VDC
Operating Free-Air Temperature Range	-55°C to +125°C
Storage Temperature	-55°C to +125°C

- 3.6 Electrical Characteristics: See Table I
- 3.6.1 Total Dose Radiation: Hybrid Microcircuit Crystal Oscillators shall be capable of meeting the electrical characteristics of Para. 3.6 after being exposed to total ionizing dose radiation of 100 krads as per MIL-STD-883, method 1019.
- 3.7 Hybrid Elements:
- 3.7.1 Quartz Crystals: High grade cultured quartz crystal shall be used. As an option, Fre-tech will use premium Q swept quartz crystal at an additional charge, refer to part numbering example in paragraph 6 to specify swept quartz crystal. Crystal element evaluation shall be in accordance with MIL-PRF-55310.
- 3.7.2 Crystal Mounting: Crystal element shall be mounted at 2 points in such a manner as to provide adequate ruggedness and performance under extreme environments specified herein.

- 3.7.3 Passive Elements: Established Reliability (ER) QPL components, failure level R minimum shall be used or element lot evaluation shall be as per MIL-PRF-55310, class S, or MIL-PRF-38534, Appendix C, Class K as applicable.
- 3.7.4 Microcircuit die shall be from lots that have passed the element evaluation per MIL-PRF-55310, Appendix B, Level S, except testing per Subgroup 5 is omitted. Subgroup 5 testing is circuit configuration dependent, therefore, it is more effectively performed at the oscillator level as explained in Paragraph 3.7.4 herein.
- 3.7.5 For Output Frequency 10 to 50 MHz, microcircuit die used in the oscillator shall be from NSC/FC 54ACT family and must be from wafer lot that has been successfully tested in the oscillator for ionizing radiation of up to100 krads Fre-tech has also performed SET & SEL testing on the microcircuit die. Test reports are available on request. For output frequencies above 50MHz, the microcircuit die shall be from 0,8 μm BiCMOS Si family and must be from wafer lots that have been successfully tested in the oscillator for ionizing radiation of up to 100Krads and is known to be Single Event Latch-up immune for LET of up to 95 Mev-cm<sup>2</sup>/mg.
- 3.7.6 Workmanship, Rework and Process controls shall be in accordance with the requirements of MIL-PRF-55310.
- 3.7.7 Lot Traceability: Production lot for these oscillators shall be homogenous. Each element used in the production lot shall be traceable to a single lot. Swept quartz shall be traceable to the quartz bar, and its applicable processing details.
- 4. Quality Assurance Provisions: The quality assurance provisions shall be per MIL-PRF-55310, except as specified herein.
- 4.1 100% Screening: The 100% screening shall be performed as per Table II. PDA requirements for nondestructive bond pull and burn-in shall be as specified below.
- 4.2 PDA for Nondestruct Bond Pull: Unless otherwise specified, PDA shall be 2% of total number of wires or 1 wire whichever is greater.
- 4.3 PDA for Burn-in: Unless otherwise specified, PDA for burn-in shall be 2% or 1 oscillator whichever is greater and shall be applicable to +23 °C and/or +25 °C static tests only. In addition Delta Calculation shall be performed after Burn-in and shall count for PDA. All measured values for Delta Calculation shall be recorded. Parts that exceed the specified delta limits shall be rejected and be counted for PDA. Delta Calculation shall be performed at 1.8/2.5/3.3 VDC for the following parameters:

Input Current	10% change Maximum
Output High Level	10% change Maximum
Output Low Level	0.1V change Maximum

- 4.4 Group A inspection shall be in accordance with MIL-PRF-55310 for product level S.
- 4.5 Group B inspection ( 30 day aging ) shall be in accordance with MIL-PRF-55310 for product level S. In order to expedite delivery, by customer request, the aging test can be ended after 15 days if the amount of frequency aging is less than 50% of the 30 day specification limit.
- 4.6 Oscillators shall be capable of meeting group C inspection per MIL-PRF-55310. Generic group C inspection data on similar parts may be used to satisfy this requirement. When specified by the Customer, Fre-tech will perform Group C testing at an additional charge.

4.7 Inspection and Test Data: For product level s ,unless otherwise specified in the purchase order, the following inspection and test data documentation shall be supplied with the parts.

Certificate of Conformance Summary of Class "S" screening Test Results PDA Calculations for Non-Destruct Bond Pull and Burn-in Summary of Elements Lot Traceability Electrical Tests before and after Burn-in Group A Inspection Summary Group B (30 day Aging) Data

4.8 The following test and inspection options are available at customer request.

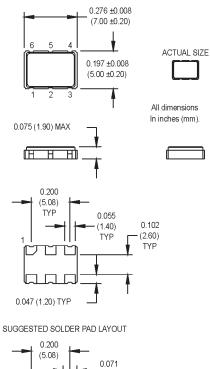
Customer Source Inspection for Pre-Cap and Final Group C Inspection per MIL-PRF-55310 on 4 or 8 units DPA (Destructive Physical Analysis) Life Test per MIL-STD-883, Method 1005, 1000 Hrs. at +125 °C MIL-PRF-38534, Group B Inspection MIL-PRF-38534, Group C Inspection

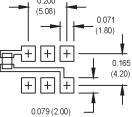
5.0 Preservation, Packaging and Packing: The oscillators shall be clean, dry and packaged in a manner to provide adequate protection against electrostatic discharge, corrosion, deterioration and physical damage during shipment.

### 6.0 Part Numbering Example:

How to order ,pls contact us at sales@freq-tech.com

### Product Dimension:





## Pin connections:

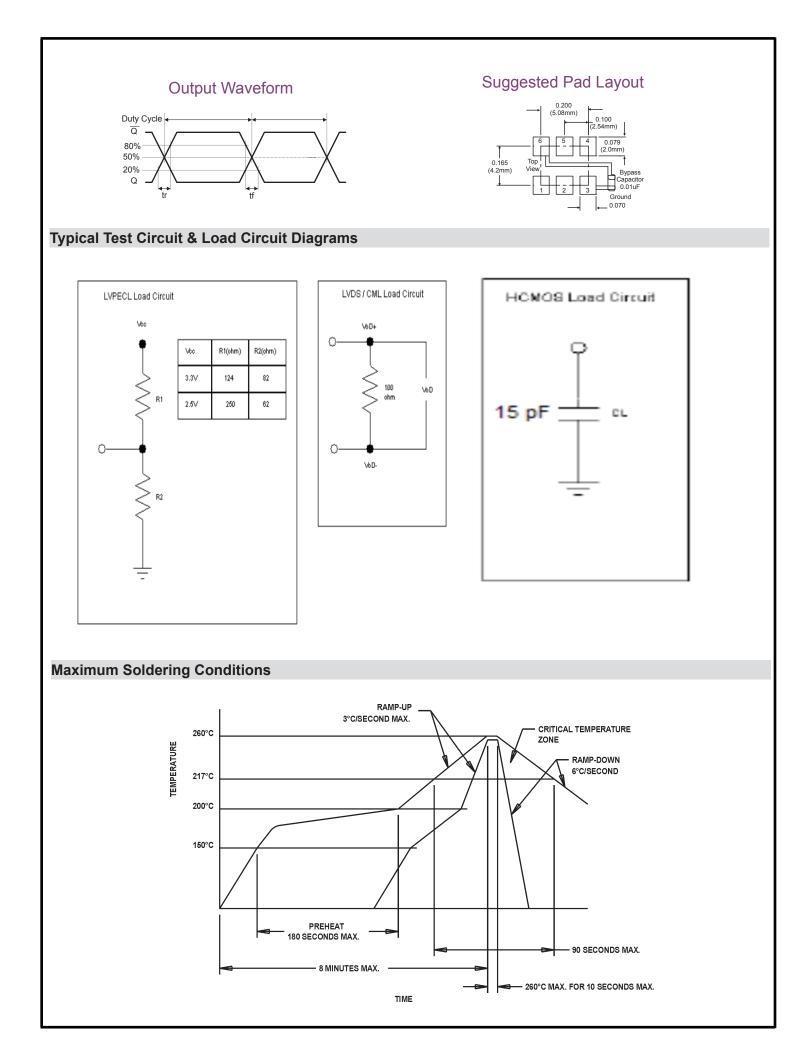
LVPECL, LVDS,CML

Pin #	Connection			
1	N/C or Vc			
2	N/C			
3	GND			
4	Output			
5	Output			
6	Supply Voltage			

#### CMOS

Pin #	Connection		
1	N/C or Vc		
2	N/C		
3	GND		
4	Output		
5*	N/C		
6	Supply Voltage		

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1	Parameter	Symbol	Min.	Тур.	Max.	Units	Conditions/Notes
ŀ	Frequency Range	F	10	Typ.	1500	MHz	LVPECL, LVDS, CML
			10		160	MHz	CMOS
Ī	Operating Temperature	T <sub>A</sub>		ow to orde		C	
	Storage Temperature	T <sub>STG</sub>	-55		+125	ĉ	
	Frequency Stability Vs Temp			w to orde		ppm	+/-(Fmax-Fmin)/(Fmax+Fmin)
	Frequency Tolerance at +25℃		-3.0		+3.0	ppm	See Note 1
	Frequency Vs. Aging		-2.0		+ 2.0	ppm	1 <sup>st</sup> year
-			-1.0		+ 1.0	ppm	Thereafter(per year).
-	Frequency Vs. Supply Voltage			± 0.5		ppm	5% voltage variation
	Frequency Vs. Reflow			± 0.80		ppm	2 reflows max.
-	Frequency Vs. Load			± 0.5		ppm	5% supply voltage variation
-	Operating Voltage	V <sub>cc</sub> /V <sub>s</sub> /V <sub>dd</sub>	3.14	3.3	3.47	V	o // oupply voltage variation
		· cc· · s· · du	2.38	2.5	2.63	v	
			1.7	1.8	1.9	V	
Ī	Operating Current	I <sub>CC</sub>			130	mA	LVPECL
					110	mA	LVDS
				1	120	mA	CML
ŝ					100	mA	CMOS
specification	Rise/Fall Time	Tr/Tf		1	1.0	ns	PECL, LVPECL, LVDS
g			14 4 00		8	ns	CMOS
CIII	Logic "1" Level	V <sub>OH</sub>	V <sub>cc</sub> -1.02			V	LVPECL
be	Logic "0" Level	V <sub>OL</sub>	90% V <sub>dd</sub>		V <sub>cc</sub> -1.63	V	CMOS LVPECL
-	Logic o Level	V <sub>OL</sub>			10% V <sub>dd</sub>	V	CMOS
Electrical	Common Mode Output Voltage	Vcm		1.2	1070 V <sub>dd</sub>	V	LVDS
BCI	Symmetry (Duty Cycle)	Vom	45	1.4	55	%	@ 50% Vdd (CMOS)
ш			45		55	%	@ 50% of waveform (LVPECL)
			45		55	%	@ 1.25 V (LVDS)
	Output Voltage Level			0.95		Vp-р	CML
	Tuning Range		± 5			ppm	VCTCXO only. See Note 2.
	Voltage Contril range	Vc	0.18	0.9	1.62	V	Ddd=1.8V Ddd=2.5V
		_	0.25 0.30	1.25 1.65	2.25 3.00	V V	Ddd=2.5V Ddd=3.3V
-			0.00	20	0.00	ps	LVPECL
	Output Skew			15		ps	CML
				20		ps	LVDS
	Output Load						See Note 3
			50 ohm to				LVPECL
				00 ohm			LVDS, CML
			Differe		-		01400
-	Enable/Disable Eurotian		15			pF	CMOS
	Enable/Disable Function		80%		0.5	V	Outputs enabled Outputs disabled
					0.5	V	Outputs enabled
			80%		0.0	v	Outputs disabled
	Phase Noise (Typical)	10 Hz	100 Hz	1 kHz	10 kHz	100 kHz	Offset from carrier
	@ 622.080 MHz (LVPECL)	-60	-90	-120	-128	-135	dBc/Hz
	@ 100.000 MHz (HCMOS)	-73	-100	-125	-130	-138	dBc/Hz
	@ 50.000 MHZ (HCMOS)	-80	-110	-130	-140	-142	dBc/Hz
	Phase jitter	0.5ps (Tv	/p)@Integra	ited,Band	width 12KHz	to 20MHz .F	RMS
	Jitter Random period jitter	1.0ps (Typ)@Integrated,Bandwidth 10KHz to 1MHz ,RMS					
	Pk to Pk jitter	20.0ps (Typ)					
ਰ	Shock	Per MIL-STD-202, Method 213, Condition C Per MIL-STD-202, Methods 201 & 204					
lental	Vibration						
Ē	Solderability	Per EIAJ-STD-002 1 X 10 <sup>-8</sup> atm cc/sec of helium (Crystal only) Per MIL-STD-883, Method 1011, Condition A Per MIL-STD-883, Method 1010, Condition B					
Environm	Hermeticity						
<u>~</u> г	Thermal Shock						
ĘΙ							

Note 1: For 10MHz to 800MHz ,±3ppm(Max),other frequencies ,±5ppm(Max) Note 2: Contact factory for other Tuning Range options.

Note 3: See Load Circuit Diagram

Table II - Class R/V/S , Screening (100%)

Test - Inspection	Test Method – Condition		
Nondestructive Bond Pull	MIL-STD-883, Method 2023		
Internal Visual	MIL-STD-883, Method 2017, Level S		
Stabilization Bake ( Prior to Seal ) <u>1</u> /	MIL-STD-883, Method 1008, Condition C ( +150 °C ), 48 hours minimum		
Thermal Shock	MIL-STD-883, Method 1011, Condition A		
Temperature Cycling	MIL-STD-883, Method 1010, Condition B		
Constant Acceleration	MIL-STD-883, Method 2001, Condition A $Y_1$ axis only ( 5000 G )		
Seal (Fine and Gross Leak)	MIL-PRF-55310, Para. 4.8.2.2.2		
Particle Impact Noise Detection ( PIND )	MIL-STD-883, Method 2020, Condition A		
Radiographic Inspection	MIL-STD-883, Method 2012, Class S		
Electrical Tests: Record all measurements.	Nominal Supply Voltage, Specified load, +23 °C		
Input Current Output Frequency Output Voltage Levels Output Rise & Fall Times Output Duty Cycle	MIL-PRF-55310, Para. 4.8.5 MIL-PRF-55310, Para. 4.8.6 MIL-PRF-55310, Para. 4.8.21.3 MIL-PRF-55310, Para. 4.8.22 MIL-PRF-55310, Para. 4.8.23		
Burn-in ( load )	+125 °C, Nominal Supply Voltage and Burn-in load, 320 Hours Minimum		
Electrical Tests: Record all measurements.	Nominal and Extreme Supply Voltages, Specified load, +23 °C and operating temperature extremes,		
Input Current Output Frequency Output Voltage Levels Output Rise & Fall Times Output Duty Cycle	MIL-PRF-55310, Para. 4.8.5 MIL-PRF-55310, Para. 4.8.6 MIL-PRF-55310, Para. 4.8.21.3 MIL-PRF-55310, Para. 4.8.22 MIL-PRF-55310, Para. 4.8.23		

<u>1</u>/ Vacuum bake and maintain oscillators in dry nitrogen per MIL-PRF-55310.

Table III - Class B/M Screening (100%)				
Test - Inspection	Test Method – Condition			
Nondestructive Bond Pull	MIL-STD-883, Method 2023 (N/A or specified in the PO)			
Internal Visual	MIL-STD-883, Method 2017, Level B			
Stabilization Bake ( Prior to Seal ) <u>1</u> /	MIL-STD-883, Method 1008, Condition C ( +150 °C ), 24 hours minimum			
Temperature Cycling	MIL-STD-883, Method 1010, Condition B			
Constant Acceleration	MIL-STD-883, Method 2001, Condition A $Y_1$ axis only ( 5000 G )			
Seal (Fine and Gross Leak)	MIL-PRF-55310, Para. 4.8.2.2.2			
Particle Impact Noise Detection ( PIND )	MIL-STD-883, Method 2020, Condition A (N/A or specified in the PO)			
Electrical Tests:	Nominal Supply Voltage, Specified load, +23 °C Verify all parameters			
Input Current Output Frequency Output Voltage Levels Output Rise & Fall Times Output Duty Cycle	MIL-PRF-55310, Para. 4.8.5 MIL-PRF-55310, Para. 4.8.6 MIL-PRF-55310, Para. 4.8.21.3 MIL-PRF-55310, Para. 4.8.22 MIL-PRF-55310, Para. 4.8.23			
Burn-in(load)	+125 °C, Nominal Supply Voltage and Burn-in load, 160 Hours Minimum			
Electrical Tests:	Nominal Supply Voltage, Specified load, +23 °C and verify frequency at temperature extremes.			
Input Current Output Frequency Output Voltage Levels Output Rise & Fall Times Output Duty Cycle	MIL-PRF-55310, Para. 4.8.5 MIL-PRF-55310, Para. 4.8.6 MIL-PRF-55310, Para. 4.8.21.3 MIL-PRF-55310, Para. 4.8.22 MIL-PRF-55310, Para. 4.8.23			

<u>1</u>/ Vacuum bake and maintain oscillators in dry nitrogen per MIL-PRF-55310.